

## 4N65Z-VB Datasheet

## N-Channel 650V (D-S) Power MOSFET

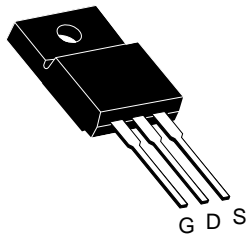
| PRODUCT SUMMARY           |                 |     |
|---------------------------|-----------------|-----|
| $V_{DS}$ (V)              | 650             |     |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10$ V | 2.5 |
| $Q_g$ (Max.) (nC)         | 48              |     |
| $Q_{gs}$ (nC)             | 12              |     |
| $Q_{gd}$ (nC)             | 19              |     |
| Configuration             | Single          |     |

## FEATURES

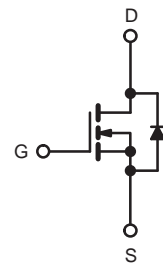
- Low Gate Charge  $Q_g$  Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Compliant to RoHS directive 2002/95/EC


**RoHS\***  
 COMPLIANT

TO-220 FULLPAK



Top View




N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted |                  |                |      |          |
|--|------------------|----------------|------|----------|
| PARAMETER  | SYMBOL           | LIMIT          | UNIT |          |
| Drain-Source Voltage   | $V_{DS}$         | 650            | V    |          |
| Gate-Source Voltage  | $V_{GS}$         | $\pm 30$       |      |          |
| Continuous Drain Current <sup>e</sup>                          | $V_{GS}$ at 10 V | $T_C = 25$ °C  | A    |          |
| Continuous Drain Current                                       |                  | $T_C = 100$ °C |      |          |
| Pulsed Drain Current <sup>a</sup>                              | $I_{DM}$         | 18             |      |          |
| Linear Derating Factor   |                  | 0.48           | W/°C |          |
| Single Pulse Avalanche Energy <sup>b</sup>                     | $E_{AS}$         | 325            | mJ   |          |
| Repetitive Avalanche Current <sup>a</sup>                      | $I_{AR}$         | 4              | A    |          |
| Repetitive Avalanche Energy <sup>a</sup>                       | $E_{AR}$         | 6              | mJ   |          |
| Maximum Power Dissipation                                      | $T_C = 25$ °C    | $P_D$          | 30   | W        |
| Peak Diode Recovery $dV/dt$ <sup>c</sup>                       |                  | $dV/dt$        | 2.8  | V/ns     |
| Operating Junction and Storage Temperature Range               | $T_J, T_{stg}$   | - 55 to + 150  | °C   |          |
| Soldering Recommendations (Peak Temperature) <sup>d</sup>      | for 10 s         | 300            |      |          |
| Mounting Torque  | 6-32 or M3 screw |                | 10   | lbf · in |
|  |                  |                | 1.1  | N · m    |

## Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting  $T_J = 25$  °C,  $L = 24$  mH,  $R_G = 25$   $\Omega$ ,  $I_{AS} = 3.2$  A (see fig. 12).
- $I_{SD} \leq 3.2$  A,  $dI/dt \leq 90$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- 1.6 mm from case.
- Drain current limited by maximum junction temperature.

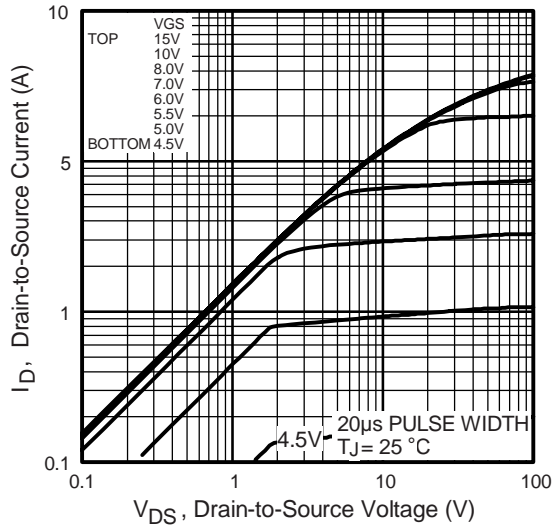
| THERMAL RESISTANCE RATINGS       |            |      |      |      |
|----------------------------------|------------|------|------|------|
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 65   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 2.1  |      |

| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted |                       |   |   |      |      |           |               |
|--|-----------------------|---|---|------|------|-----------|---------------|
| PARAMETER  | SYMBOL                | TEST CONDITIONS   |   | MIN. | TYP. | MAX.      | UNIT          |
| <b>Static</b>  |                       |   |   |      |      |           |               |
| Drain-Source Breakdown Voltage   | $V_{DS}$              | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$   |   | 650  | -    | -         | V             |
| $V_{DS}$ Temperature Coefficient   | $\Delta V_{DS}/T_J$   | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}^d$   |   | -    | 670  | -         | mV/°C         |
| Gate-Source Threshold Voltage  | $V_{GS(th)}$          | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$   |   | 2.0  | -    | 4.0       | V             |
| Gate-Source Leakage  | $I_{GSS}$             | $V_{GS} = \pm 30\text{ V}$  |   | -    | -    | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current  | $I_{DSS}$             | $V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$  |   | -    | -    | 25        | $\mu\text{A}$ |
|  |                       | $V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$   |   | -    | -    | 250       |               |
| Drain-Source On-State Resistance   | $R_{DS(on)}$          | $V_{GS} = 10\text{ V}$  | $I_D = 3.1\text{ A}^b$  | -    | 2.5  | -         | $\Omega$      |
| Forward Transconductance   | $g_{fs}$              | $V_{DS} = 50\text{ V}, I_D = 3.1\text{ A}$  |   | 3.9  | -    | -         | S             |
| <b>Dynamic</b>   |                       |   |   |      |      |           |               |
| Input Capacitance  | $C_{iss}$             | $V_{GS} = 0\text{ V},$<br>$V_{DS} = 25\text{ V},$<br>$f = 1.0\text{ MHz}$ , see fig. 5  |   | -    | 1080 | -         | pF            |
| Output Capacitance   | $C_{oss}$             |   |   | -    | 177  | -         |               |
| Reverse Transfer Capacitance   | $C_{rss}$             |   |   | -    | 7.0  | -         |               |
| Output Capacitance   | $C_{oss}$             | $V_{GS} = 0\text{ V}$   | $V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$                                   | -    | 1912 | -         | pF            |
|  |                       |   | $V_{DS} = 520\text{ V}, f = 1.0\text{ MHz}$                                   | -    | 48   | -         |               |
| Effective Output Capacitance   | $C_{oss\text{ eff.}}$ | $V_{DS} = 0\text{ V to } 520\text{ V}^c$  |   | -    | 84   | -         |               |
| Total Gate Charge  | $Q_g$                 | $V_{GS} = 10\text{ V}$  | $I_D = 3.2\text{ A}, V_{DS} = 400\text{ V}$<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 48        | nC            |
| Gate-Source Charge   | $Q_{gs}$              |   |   | -    | -    | 12        |               |
| Gate-Drain Charge  | $Q_{gd}$              |   |   | -    | -    | 19        |               |
| Turn-On Delay Time   | $t_{d(on)}$           | $V_{DD} = 325\text{ V}, I_D = 3.2\text{ A}$<br>$R_G = 9.1\text{ }\Omega, R_D = 62\text{ }\Omega,$<br>see fig. 10 <sup>b</sup>                           |   | -    | 14   | -         | ns            |
| Rise Time  | $t_r$                 |   |   | -    | 20   | -         |               |
| Turn-Off Delay Time  | $t_{d(off)}$          |   |   | -    | 34   | -         |               |
| Fall Time  | $t_f$                 |   |   | -    | 18   | -         |               |
| <b>Drain-Source Body Diode Characteristics</b>                           |                       |   |   |      |      |           |               |
| Continuous Source-Drain Diode Current                                    | $I_S$                 | MOSFET symbol showing the integral reverse p - n junction diode<br> | -   | -    | 4    | A         |               |
| Pulsed Diode Forward Current <sup>a</sup>                                | $I_{SM}$              |   | -   | -    | 21   |           |               |
| Body Diode Voltage   | $V_{SD}$              | $T_J = 25\text{ }^\circ\text{C}, I_S = 3.2\text{ A}, V_{GS} = 0\text{ V}^b$   |   | -    | -    | 1.5       | V             |
| Body Diode Reverse Recovery Time   | $t_{rr}$              | $T_J = 25\text{ }^\circ\text{C}, I_F = 3.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$  |   | -    | 493  | 739       | ns            |
| Body Diode Reverse Recovery Charge                                       | $Q_{rr}$              |   |   | -    | 2.1  | 3.2       | $\mu\text{C}$ |
| Forward Turn-On Time   | $t_{on}$              | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )   |   |      |      |           |               |

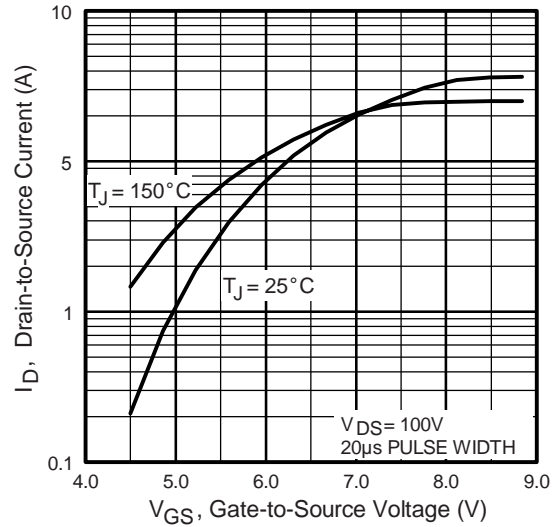
**Notes**

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .
- $t = 60\text{ s}, f = 60\text{ Hz}$ .

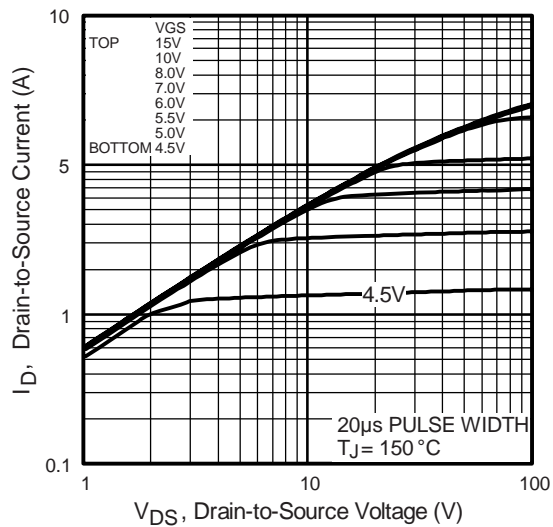
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



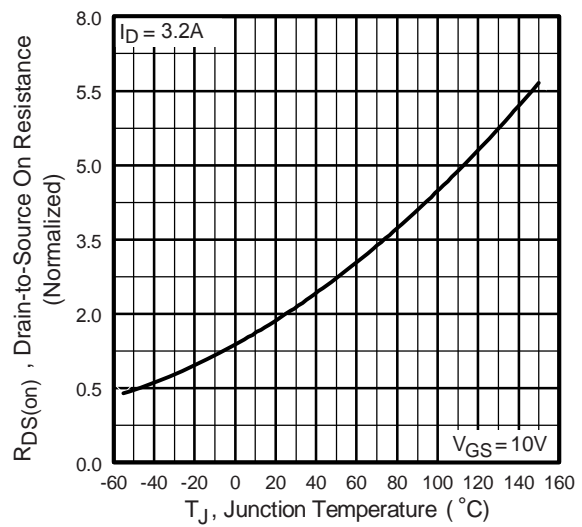
**Fig. 1 - Typical Output Characteristics**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 2 - Typical Output Characteristics**



**Fig. 4 - Normalized On-Resistance vs. Temperature**

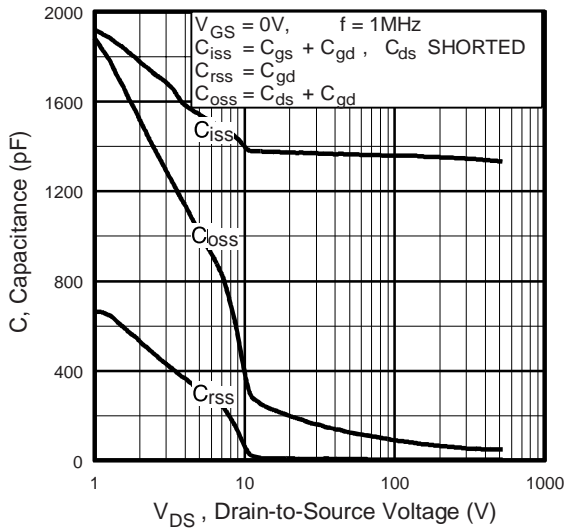


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

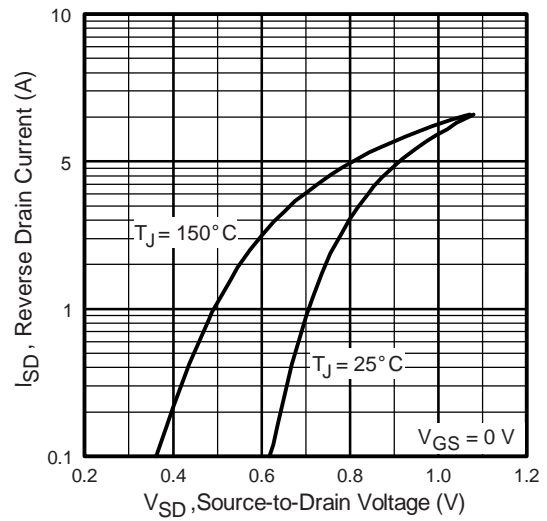


Fig. 7 - Typical Source-Drain Diode Forward Voltage

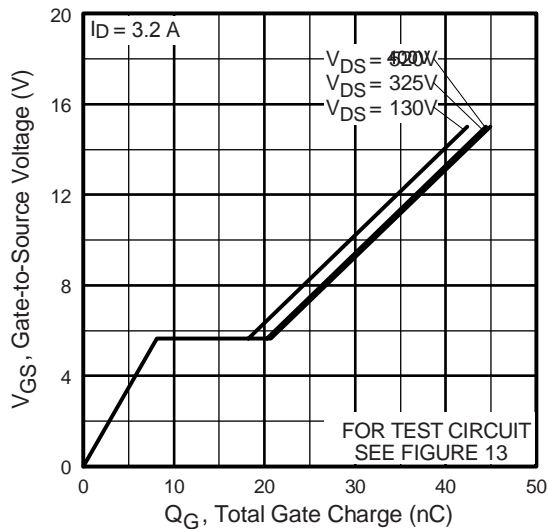


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

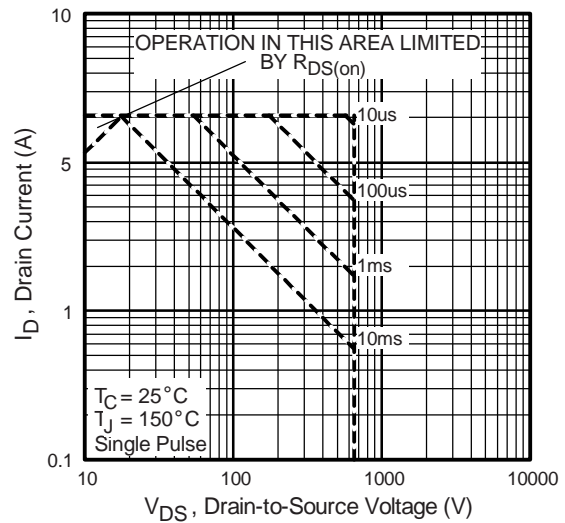


Fig. 8 - Maximum Safe Operating Area

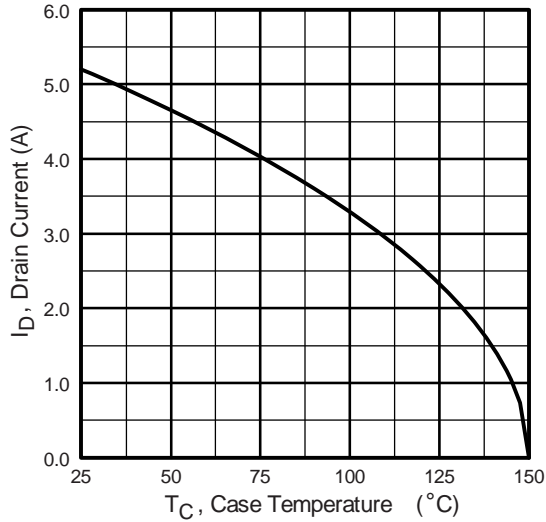


Fig. 9 - Maximum Drain Current vs. Case Temperature

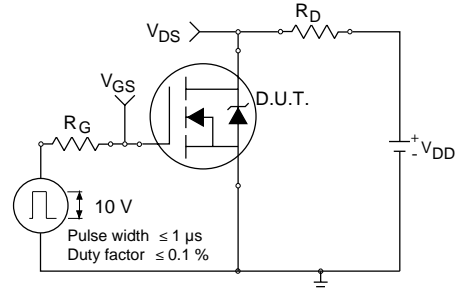


Fig. 10a - Switching Time Test Circuit

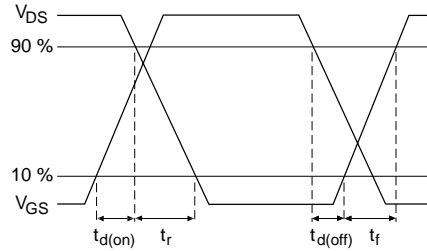


Fig. 10b - Switching Time Waveforms

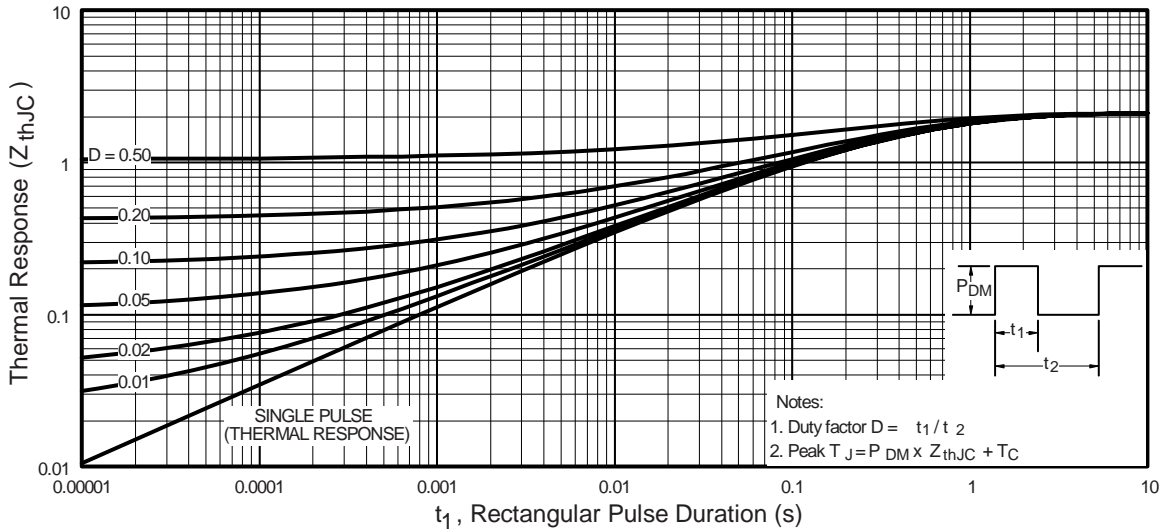


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

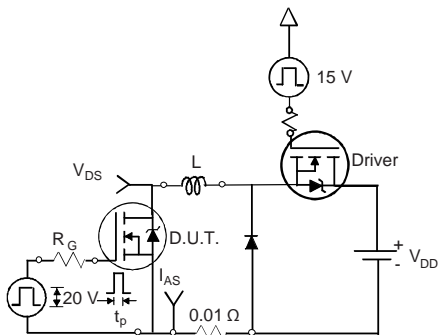


Fig. 12a - Unclamped Inductive Test Circuit

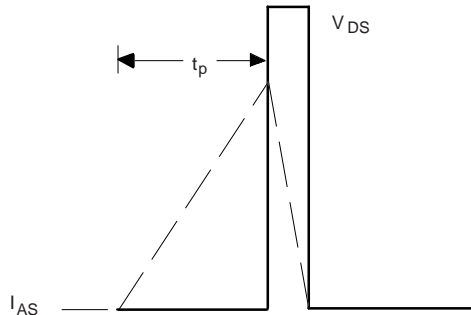


Fig. 12b - Unclamped Inductive Waveforms

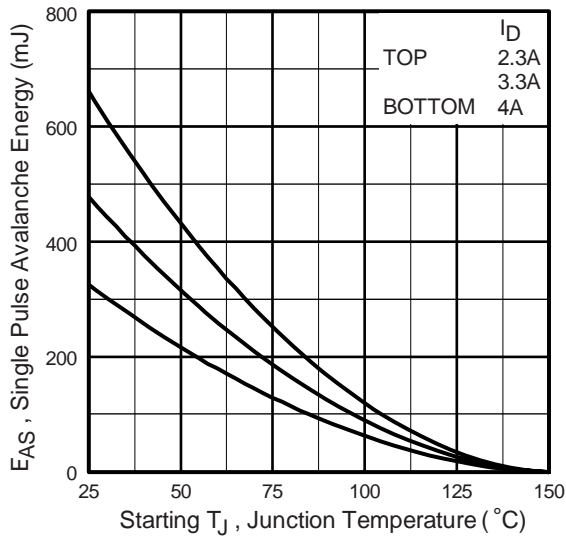


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

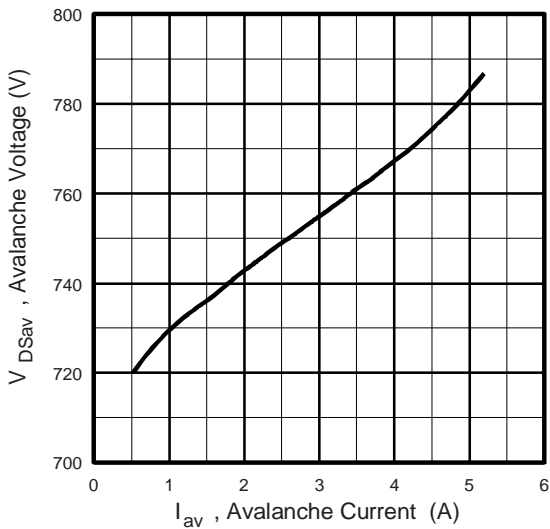


Fig. 12d - Typical Drain-to Source Voltage vs. Avalanche Current

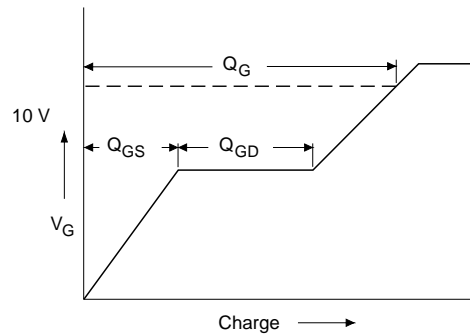


Fig. 13a - Basic Gate Charge Waveform

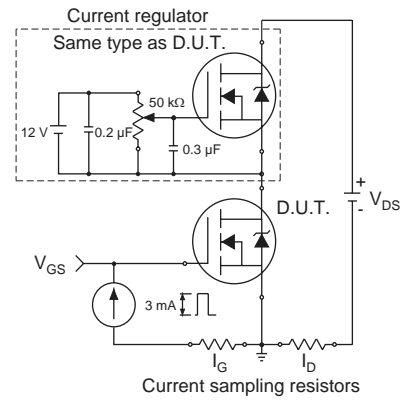
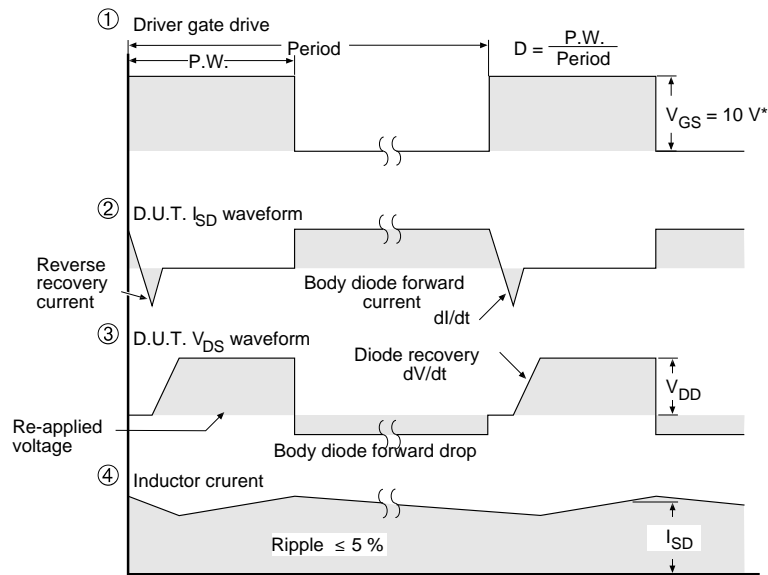
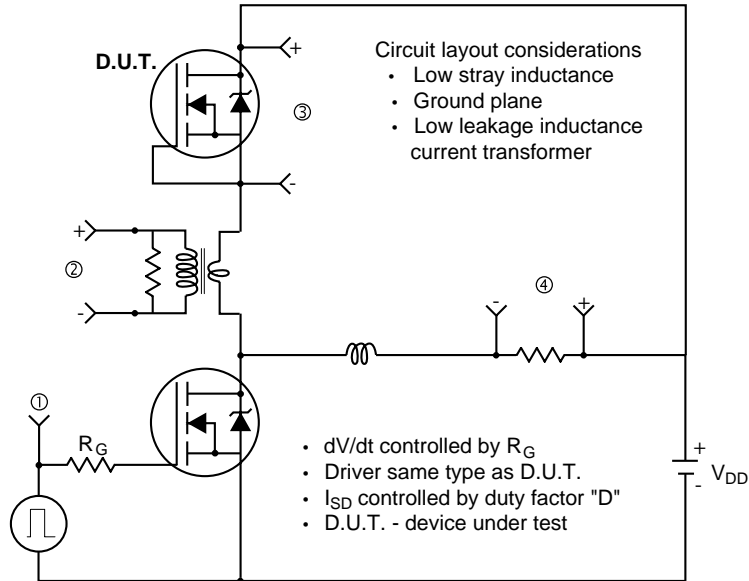


Fig. 13b - Gate Charge Test Circuit

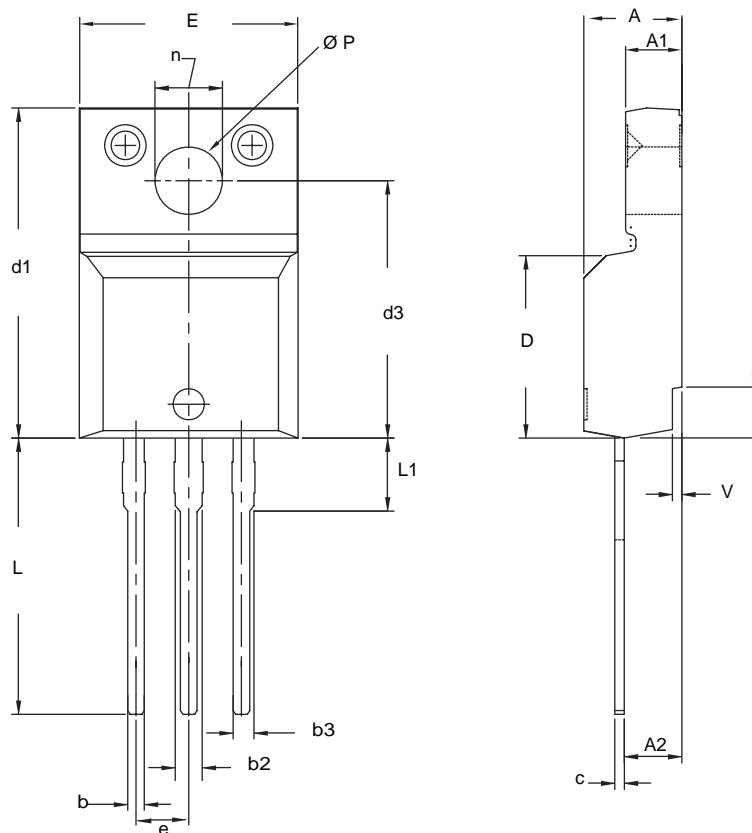
### Peak Diode Recovery dV/dt Test Circuit



\*  $V_{GS} = 5 V$  for logic level devices

Fig. 14 - For N-Channel

**TO-220 FULLPAK (HIGH VOLTAGE)**



| DIM. | MILLIMETERS |        | INCHES    |       |
|------|-------------|--------|-----------|-------|
|      | MIN.        | MAX.   | MIN.      | MAX.  |
| A    | 4.570       | 4.830  | 0.180     | 0.190 |
| A1   | 2.570       | 2.830  | 0.101     | 0.111 |
| A2   | 2.510       | 2.850  | 0.099     | 0.112 |
| b    | 0.622       | 0.890  | 0.024     | 0.035 |
| b2   | 1.229       | 1.400  | 0.048     | 0.055 |
| b3   | 1.229       | 1.400  | 0.048     | 0.055 |
| c    | 0.440       | 0.629  | 0.017     | 0.025 |
| D    | 8.650       | 9.800  | 0.341     | 0.386 |
| d1   | 15.88       | 16.120 | 0.622     | 0.635 |
| d3   | 12.300      | 12.920 | 0.484     | 0.509 |
| E    | 10.360      | 10.630 | 0.408     | 0.419 |
| e    | 2.54 BSC    |        | 0.100 BSC |       |
| L    | 13.200      | 13.730 | 0.520     | 0.541 |
| L1   | 3.100       | 3.500  | 0.122     | 0.138 |
| n    | 6.050       | 6.150  | 0.238     | 0.242 |
| Ø P  | 3.050       | 3.450  | 0.120     | 0.136 |
| u    | 2.400       | 2.500  | 0.094     | 0.098 |
| v    | 0.400       | 0.500  | 0.016     | 0.020 |

ECN: X09-0126-Rev. B, 26-Oct-09  
DWG: 5972

**Notes**

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet  $C_{pk} > 1.33$ .
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.



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